

- Low noise
- Blue enhanced
- High shunt resistance •
- **High response** •

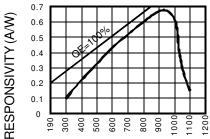
The PDB-V106 is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for low noise photovoltaic applications. Packaged in a hermetic TO-5 metal can with a flat window.

- Instrumentation
- Industrial controls
- Laser detection
- Flame detection

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
VBR	Reverse Voltage		75	V	
T _{STG}	Storage Temperature	-55	+150	S	
То	Operating Temperature Range	-40	+125	с	
Ts	Soldering Temperature*		+240	с	
Ι	Light Current		500	mA	

SPECTRALRESPONSE



WAVELENGTH(nm)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current	H = 100 fc, 2850 K	100	125		μA
l d	Dark Current	$H = 0, V_{R} = 10 V$		300	500	pА
Rsh	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$.2	2		GΩ
TC RSH	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_{R} = 0 V^{**}$		1200		pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	I = 10 µµA	30	50		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		1.0x10 ⁻¹⁴		W/ V Hz
tr	Response Time	$RL = 1 K\Omega V_R = 0 V$		800		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz [FORM NO. 100-PDB-V106 REV C]